

Title (en)

SEMICONDUCTOR STRUCTURES HAVING A STRAIN COMPENSATED LAYER AND METHOD OF FABRICATION

Title (de)

HALBLEITERSTRUKTUREN MIT EINER SPANNUNGSKOMPENSIERTEN SCHICHT UND HERSTELLUNGSVERFAHREN

Title (fr)

STRUCTURES DE SEMI-CONDUCTEUR POSSEDANT UNE COUCHE A CONTRAINTES COMPENSEES ET PROCEDE DE FABRICATION ASSOCIE

Publication

EP 1183761 A2 20020306 (EN)

Application

EP 00940681 A 20000301

Priority

- IB 0000892 W 20000301
- US 27731999 A 19990326

Abstract (en)

[origin: WO0058999A2] The present invention provides a semiconductor structure which includes a strain compensated superlattice layer comprising a plurality of pairs of constituent layers, with the first constituent layer comprising a material under tensile stress, and the second constituent layer comprising a material under compressive stress, such that the stresses of the adjacent layer compensate one another and lead to reduced defect generation. Appropriate selection of materials provides increased band gap and optical confinement in at least some implementations. The structure is particularly suited to the construction of laser diodes, photodiodes, phototransistors, and heterojunction field effect and bipolar transistors.

IPC 1-7

H01S 5/34; **H01L 29/15**; **H01L 31/0352**; **H01L 33/00**

IPC 8 full level

H01L 21/331 (2006.01); **H01L 21/205** (2006.01); **H01L 21/338** (2006.01); **H01L 29/201** (2006.01); **H01L 29/737** (2006.01); **H01L 29/778** (2006.01); **H01L 29/812** (2006.01); **H01L 33/06** (2010.01); **H01L 33/32** (2010.01); **H01S 5/323** (2006.01); **H01S 5/343** (2006.01); **H01L 31/11** (2006.01)

CPC (source: EP)

B82Y 20/00 (2013.01); **H01L 31/03048** (2013.01); **H01L 31/035236** (2013.01); **H01L 31/1105** (2013.01); **H01L 33/06** (2013.01); **H01L 33/32** (2013.01)

Citation (search report)

See references of WO 0058999A2

Designated contracting state (EPC)

DE FR GB

DOCDB simple family (publication)

WO 0058999 A2 20001005; **WO 0058999 A3 20010104**; **WO 0058999 A9 20020829**; **WO 0058999 B1 20010802**; CN 1347581 A 20020501; EP 1183761 A2 20020306; JP 2002540618 A 20021126

DOCDB simple family (application)

IB 0000892 W 20000301; CN 00805556 A 20000301; EP 00940681 A 20000301; JP 2000608410 A 20000301